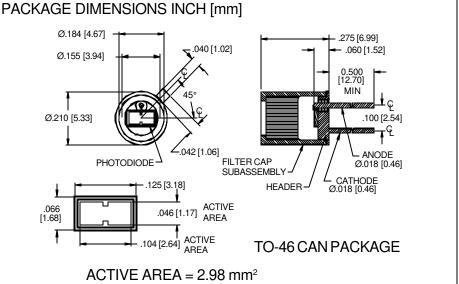
PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic DETECTORS INC. (center wavelength 950 nm) Type PDI-V495-46





RESPONSIVITY (A/W)

FEATURES

- 950 nm CWL
- 65 nm FWHM
- Large active area
- Matched to 940 nm LEDs •

The **PDI-V495-46** is a silicon, PIN planar diffused, photodiode with a wide band interferance filter. The detector filter combination has a wide 65 nm half bandwidth designed for low noise photovoltaic applications. Packaged in a TO-46 metal can. **ABSOLUTE MAXIMUM RATING** (TA=25°C unless otherwise noted)

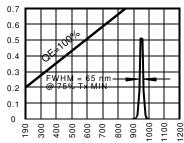
APPLICATIONS

- Spectrophotometry
- Chemistry instrumentation
- I.R. detector
- GaAs LED sensor ۰

SPECTRAL RESPONSE

SYMBOL	PARAMETER	MIN	MAX	UNITS			
VBR	Reverse Voltage		75	V			
T _{STG}	Storage Temperature	-20	+85	°C			
To	Operating Temperature Range	-15	+70	°C			
Ts	Soldering Temperature*		+240	°C			
Ι	Light Current		0.5	mA			

DESCRIPTION



WAVELENGTH (nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	35	40		μA
ΙD	Dark Current	$H = 0, V_{R} = 10 V$		150	300	pА
Rsн	Shunt Resistance	H = 0, V _R = 10 mV	1.0	6		GΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		340		рF
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		950		nm
HBW	Half Bandwidth	(FWHM)		65		nm
VBR	Breakdown Voltage	I = 10 µµA	30	50		V
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		5x10 ⁻¹⁴		W/ / Hz
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		450		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz, ***without filter [FORM NO. 100-PDI-V495-46 REVA [FORMNO.100-PDI-V495-46 REVA]